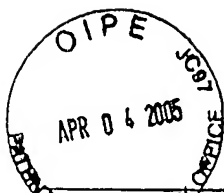


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Form PTO 1549 (Rev. 2-32)				U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. MAN-013		Serial No. 10/723,285	
Information Disclosure Statement by Applicant						Applicant: Werner, et al.			
(Use several sheets if necessary)						Filed: November 25, 2003		Group: 2811	
U.S. Patent Documents									
Init.		Document No.	Date	Name	Class	Subclass	Filing Date		
Foreign Documents									
								Translation	
Init.		Document No.	Date	Country	Class	Subclass	Yes	No	
SA	1.	102 07 952 A1	09/04/03	DE	H 01 L	21/3063		X	
Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)									
SA	2.	L. Colace et al., "Efficient high-speed near-infrared Ge photodetectors integrated on Si substrates", <u>Applied Physics Letters</u> , pgs. 1231-1233, 6 March 2000.							
	3.	A.G. Cullis et al., "The structural and luminescence properties of porous silicon", <u>Applied Physics Reviews</u> , pgs. 909-965 1 August 1997.							
	4.	H. Presting et al., "Room-temperature electroluminescence from Si/Ge/Si <sub>1-x</sub> Ge <sub>x</sub> quantum-well diodes grown by molecular-beam epitaxy", <u>Applied Physics Letters</u> , pgs. 2376-2378, 14 October 1996.							
	5.	T. Brunhes et al., "Electroluminescence of Ge/Si self-assembled quantum dots grown by chemical vapor deposition", <u>Applied Physics Letters</u> , pgs. 1822-1824, 18 September 2000.							
	6.	E. Eberl et al., "Pseudomorphic Si <sub>1-y</sub> C <sub>y</sub> and Si <sub>1-x-y</sub> Ge <sub>x</sub> C <sub>y</sub> alloy layers on Si", <u>Thin Solid Films</u> , pgs. 98-104, 1997.							
	7.	O.G. Schmidt et al., "Multiple layers of self-assembled Ge/Si islands: Photoluminescence, strain fields, material interdiffusion, and island formation", <u>Physical Review B</u> , pgs. 721-729, 15 May 2000.							
	8.	M. Goryll et al., "Morphology and photoluminescence of Ge islands grown on Si(001)", <u>Thin Solid Films</u> , pgs. 244-247, 1998.							
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Examiner <i>Shoismere</i>					Date Considered <i>6/27/05</i>				
Examiner: Initial if citation considered; whether or not citation is in conference with MPEP 609; Draw line through citation if not conformance and not considered. Include a copy of this form with the next communication to applicant.									